	Type	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors	Ref #
1	BRS	16	stack$ with semiconductor near layer with selective near etch$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/20 00:13				S3
2	BRS	136	semiconductor near layer with selective near etch$5 and optic$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/20 00:14				S4
3	BRS	15	stack$5 with semiconductor with selective near etch$5 and optic$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/20 00:18				S5
4	BRS	7	stack$5 with semiconductor with selective with etch$5 with lateral$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/20 00:26				S7
5	BRS	163	semiconductor and selective with etch$5 with lateral$4 and optic$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/20 00:26				S8
6	BRS	127	semiconductor with layer and selective with etch$5 with lateral$4 and optic$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/20 00:26				S9

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors	Ref #
7	BRS	11	semiconductor with layer and selective with etch$5 with lateral$4 and optic$5 and air near gap	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/27 23:40				S10
8	BRS	24	selectiv$4 with etch$5 with lateral$4 and optic$5 and air near gap	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/27 23:48				S11
9	BRS	4	selectiv$4 with etch$5 with lateral$4 and optic$5 and fill$4 with air near gap	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/27 23:52				S12
10	BRS	7	selectiv$4 with etch$5 with lateral$4 and fill$4 with air near gap	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/27 23:50				S13
11	BRS	12	stack with selectiv$4 with etch$5 with lateral$4 and optic$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/27 23:56				S14

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors	Ref #
12	BRS	44	stack with alternat$4 and selectiv$4 with etch$5 with lateral$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/28 00:13				S15
13	BRS	146	selectiv$4 with etch$5 with lateral$4 same fill$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/28 00:14				S16
14	BRS	22	selectiv$4 with etch$5 with lateral$4 same fill$5 and optic$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/28 00:23				S17
15	BRS	215	etch$5 with lateral$4 same fill$5 and optic$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/28 00:23				S18
16	BRS	10	etch$5 with lateral$4 same fill$5 and optic$4 and air near gap	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/28 00:23				S19
17	BRS	1	stack$ with selective near etch$5 near lateral$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/28 00:26				S20
18	BRS	2	stack$4 with selectiv$4 near etch$5 near lateral$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/28 00:27				S21

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors	Ref #
19	BRS	70	selectiv$4 near etch$5 near lateral$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/28 00:28				S22
20	BRS	3	("438"/$).ccls. and stack$ and selectiv$ near etch$5 near lateral$ and optic$	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/28 00:41				S24
21	BRS	12	("438"/$).ccls. and etch$5 near lateral$ and optic$ and vcsel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/28 00:44				S25
22	BRS	36	("438"/$).ccls. and stack$ near selectiv$ near etch$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/28 00:48				S23
23	BRS	83	epitaxial near liftoff and optic$	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/28 00:51			'	S26
24	BRS	19	epitaxial near liftoff and optic$ and air near gap	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/28 00:51				S27
25	BRS	18	epitaxial near liftoff and etch$ near lateral$	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/28 00:52				S28